OPA8780HP

Infrared LED Chip

High Speed

GaAlAs/GaAlAs

1. Material

Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

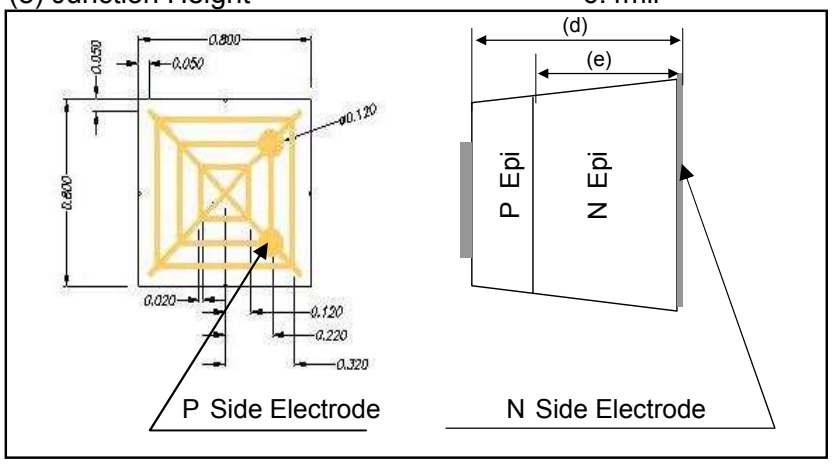
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.35	1.5	V	IF=10mA
	$V_{F(2)}$		1.5	1.7	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	2.0	3.0		mW	IF=20mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	Tr		15		ns	
Fall Time	Tf		6.3		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data

(a) Emission Area ---------- 30.5mil x 30.5mil
(b) Bottom Area ---------- 31.5mil x 31.5mil
(c) Bonding Pad ---------- 120um
(d) Chip Thickness ---------- 7mil
(e) Junction Height ---------- 6.4mil



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